

## **AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions and listings of claims in the application:

1. (Currently Amended) An etching method for etching an etching target film formed on an SiO<sub>2</sub> film placed inside an airtight processing chamber, the method comprising:

introducing a processing gas into said airtight processing chamber, wherein said processing gas contains N<sub>2</sub> and at least one of C<sub>4</sub>F<sub>8</sub> and CF<sub>4</sub>;

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic ~~target~~ film containing Si formed on the SiO<sub>2</sub> film to the point until the SiO<sub>2</sub> film is exposed, wherein a resist is used as a mask on said etching target film and the etching process ceases once the SiO<sub>2</sub> is exposed.

2. (Previously Presented) An etching method according to claim 1, wherein said organic film containing Si is constituted of SiO<sub>2</sub> containing C and H.

3. (Previously Presented) An etching method according to claim 1, wherein the dielectric constant of said organic film containing Si is equal to or lower than 3.0.

4. (Previously Presented) An etching method according to claim 1, wherein said organic target film containing Si is an organic polysiloxane film.

5. (Previously Presented) An etching method according to claim 1, wherein said processing gas further contains Ar.

Claims 6-13 (Cancelled)

14. (Currently Amended) An etching method for etching an etching target film formed on an SiO<sub>2</sub> film placed inside an airtight processing chamber, the method comprising:

introducing a processing gas into said airtight processing chamber, wherein said processing gas contains at least CF<sub>4</sub> and N<sub>2</sub>, wherein the flow rate ratio of CF<sub>4</sub> and N<sub>2</sub> in said processing gas is essentially set within a range of  $1 \leq (\text{N}_2 \text{ flow rate} / \text{CF}_4 \text{ flow rate}) \leq 4$ ;

generating a plasma in said airtight processing chamber for etching said etching target film, and

etching an organic ~~target~~ film containing Si formed on the SiO<sub>2</sub> film to the point until the SiO<sub>2</sub> film is exposed, wherein a resist is used as a mask on said etching target film and the etching process ceases once the SiO<sub>2</sub> is exposed.

Claims 15 -17 (Cancelled)